

## **GLF1110, GLF1111**

## Nano-Current Power I<sub>Q</sub>Smart<sup>™</sup> Load Switch

**Product Specification** 

## DESCRIPTION

The GLF1110 / GLF1111 is an ultra-efficiency, 2 A rated, Load Switch with integrated slew rate control. The best in class efficiency makes it an ideal choice for use in IoT, mobile, and wearable electronics.

The GLF1110 / GLF1111 features ultra-efficient  $I_QSmart^{TM}$  technology that supports the lowest quiescent current ( $I_Q$ ) and shutdown current ( $I_{SD}$ ) in the industry. Low  $I_Q$  and  $I_{SD}$  solutions help designers to reduce parasitic leakage current, improve system efficiency, and increase battery lifetime.

The integrated slew rate control can also enhance system reliability by mitigating bus voltage swings during switching events. Where uncontrolled switches can generate high inrush currents that result in voltage droop and/or bus reset events, the GLF slew rate control specifically limits inrush currents during turn-on to minimize voltage droop.

The GLF1110 / GLF1111 supports an industry leading wide input voltage range and helps to improve operating life and system robustness. Furthermore, one device can be used in multiple voltage rail applications which helps to simplify inventory management and reduce operating cost.

### **FEATURES**

• Wide Input Range: 1.5 V to 5.5 V

6 V abs max

•  $R_{ON}$ : 54 m $\Omega$  Typ @ 5.5  $V_{IN}$ 

• I<sub>OUT</sub> Max: 2 A

• Ultra-Low  $I_Q$ : 2 nA Typ @ 5.5  $V_{IN}$ 

• Ultra-Low I<sub>SD</sub>: 13 nA Typ @ 5.5 V<sub>IN</sub>

Controlled Rise Time: 600 µs at 3.3 V<sub>IN</sub>

Internal EN Pull-Down Resistor

 Integrated Output Discharge Switch: GLF1111

Wide Operating Temperature Range:

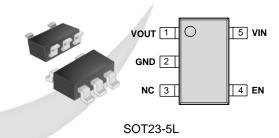
-40 °C ~ 85 °C

HBM: 4 kV, CDM: 2 kV

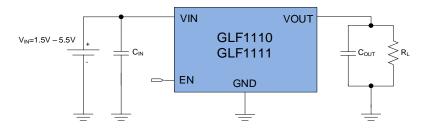
## **APPLICATIONS**

- Telecommunication Module
- Low Power Subsystem
- Mobile Devices

## **PACKAGE**



## APPLICATION DIAGRAM



## **ALTERNATE DEVICE OPTIONS**

Part Number	Top Mark	R <sub>ON</sub> (Typ) at 5.5 V	Output Discharge	EN Activity
GLF1110-T1G7	DK	54 mΩ	NA	High
GLF1111-T1G7	DL	54 mΩ	85 Ω	High

## **FUNCTIONAL BLOCK DIAGRAM**

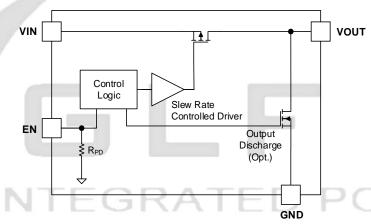


Figure 1. Functional Block Diagram

## **PIN CONFIGURATION**

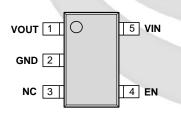


Figure 2. SOT23-5L

## **PIN DEFINITION**

Pin#	Name	Description
1	Vout	Switch Output
2	GND	Ground
3	NC	No connection
4	EN	Enable to control the switch
5	V <sub>IN</sub>	Switch Input. Supply Voltage for IC

## ABSOLUTE MAXIMUM RATINGS

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions; extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol	Pa	Min.	Max.	Unit	
V <sub>IN</sub>	VIN, VOUT, VEN tO GND			6	V
Іоит	Maximum Continuous Switch Current			2	Α
PD	Power Dissipation at T <sub>A</sub> = 25 °C			1.0	W
T <sub>STG</sub>	Storage Junction Temperature			150	°C
TA	Operating Temperature Range			85	°C
θјс	Thermal Resistance, Junction to Case			90	°C/W
$\theta_{JA}$	Thermal Resistance, Junction to Ambient			180	°C/W
FOD	Floatroatatic Discharge Conshility	Human Body Model, JESD22-A114	4		IAV /
ESD	Electrostatic Discharge Capability  Charged Device Model, JESD22-C101				kV

## RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min.	Max.	Unit
Vin	Supply Voltage	1.5	5.5	V
TA	Ambient Operating Temperature	-40	+85	°C

## **ELECTRICAL CHARACTERISTICS**

Values are at  $V_{IN}$  = 3.3 V and  $T_A$  = 25 °C unless otherwise noted.

Symbol	Parameter	Conditions		Min.	Тур.	Max.	Units
Basic Ope	eration						
VIN	Supply Voltage			1.5		5.5	V
Ια	Quiescent Current (1)	EN = Enable, I <sub>OUT</sub> =0 mA, V <sub>IN</sub> = V <sub>EN</sub> =	=5.5V		2		
iq	Quiescent Current	EN=Enable, Iout=0 mA, Vin=Ven=5.5	5V, Ta=85°C <sup>(4)</sup>		8.5		
		EN = Disable, I <sub>OUT</sub> =0 mA, V <sub>IN</sub> =1.5 V			2		
		EN = Disable, I <sub>OUT</sub> =0 mA, V <sub>IN</sub> =3.3 V			3		nA
I <sub>SD</sub>	Shut Down Current	EN = Disable, I <sub>OUT</sub> =0 mA, V <sub>IN</sub> =4.5 V			5		
		EN = Disable, I <sub>OUT</sub> =0 mA, V <sub>IN</sub> =5.5 V		13			
		EN = Disable, I <sub>OUT</sub> =0 mA, V <sub>IN</sub> =5.5 V		280			
	On-Resistance	$V_{\text{IN}}$ =5.5 V, $I_{\text{OUT}}$ = 500 mA $Ta$ =25 °C $Ta$ =85 °C $Ta$	Ta=25 °C		54		mΩ
			Ta=85 °C <sup>(4)</sup>		63		
Ron		$V_{\text{IN}=3.3}$ V, $I_{\text{OUT}=}$ 500 mA $Ta=25$ °C $Ta=85$ °C $^{(4)}$	Ta=25 °C		64		
			Ta=85 °C (4)		75		
		V <sub>IN</sub> =1.5 V, I <sub>OUT</sub> = 100 mA	Ta=25 °C		116		
Rosc	Output Discharge Resistance	E <sub>N</sub> =Low , I <sub>FORCE</sub> = 10 mA, GLF1111			85		Ω
\/	EN Input Logic High Voltage	V <sub>IN</sub> =1.5 V - 1.8 V		0.9			V
ViH		V <sub>IN</sub> =1.8 V - 5.5 V	1.2			V	
V	EN Input Logic Low	V <sub>IN</sub> =1.5 V – 1.8 V				0.3	V
$V_{IL}$	Voltage	V <sub>IN</sub> =1.8 V - 5.5 V			0.4	V	



# GLF1110, GLF1111 Nano-Current Power I<sub>Q</sub>Smart<sup>™</sup> Load Switch

R <sub>EN</sub>	EN pull down resistance	Internal Resistance		10		МΩ
I <sub>EN</sub>	EN Current	E <sub>N</sub> =5.5 V		0.5		μΑ
Switchin	Switching Characteristics (2, 3)					
t <sub>dON</sub>	Turn-On Delay	D: 450 O C: 04 UF		450		
t <sub>R</sub>	Vout Rise Time	RL=150 Ω, C <sub>OUT</sub> =0.1 μF		600		μs
tdOFF	Turn-Off Delay (4)	B150 O. C 0.1 u.E.: CI E1110		17		
t <sub>F</sub>	Vout Fall Time (4)	R <sub>L</sub> =150 Ω, C <sub>OUT</sub> =0.1 μF : GLF1110		32		
tdOFF	Turn-Off Delay (4)	B150 O. C 0.1 uE : CL E1111		17		μs
t <sub>F</sub>	V <sub>OUT</sub> Fall Time (4)	R <sub>L</sub> =150 Ω, C <sub>OUT</sub> =0.1 μF : GLF1111		12		]

Notes:

- 1. I<sub>Q</sub> does NOT include Enable pull down current through the pull-down resistor R<sub>PD</sub>.

- 2. toN = t<sub>dON</sub> + t<sub>R</sub>, toFF = t<sub>dOFF</sub> + t<sub>F</sub>
  3. Output discharge path is enabled during off.
  4. By design; characterized, not production tested

## **TIMING DIAGRAM**

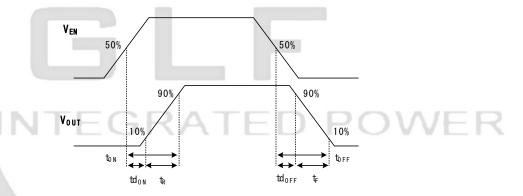


Figure 3. Timing Diagram



## TYPICAL PERFORMANCE CHARACTERISTICS

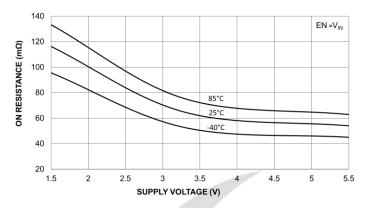


Figure 4. On-Resistance vs. Supply Voltage

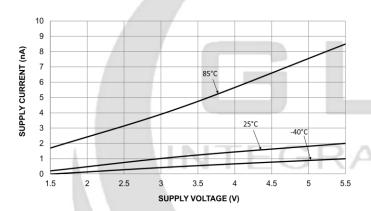


Figure 6. Quiescent Current vs. Supply Voltage

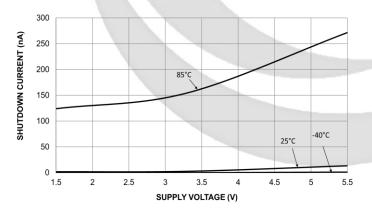


Figure 8. Shutdown Current vs. Input Voltage

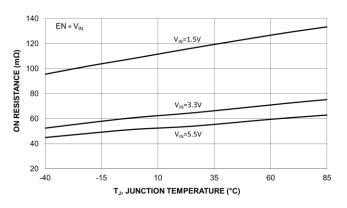


Figure 5. On-Resistance vs. Temperature

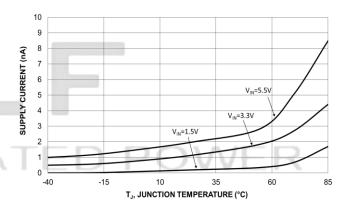


Figure 7. Quiescent Current vs. Temperature

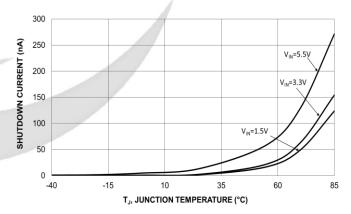


Figure 9. Shutdown Current vs. Temperature

# GLF1110, GLF1111 Nano-Current Power I<sub>Q</sub>Smart<sup>™</sup> Load Switch

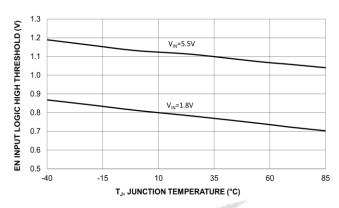


Figure 10. EN Input Logic High Threshold Vs. Temperature

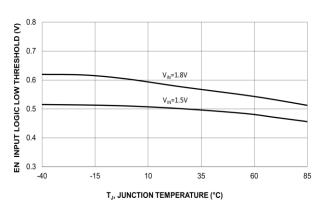


Figure 11. EN Input Logic Low Threshold Vs. Temperature

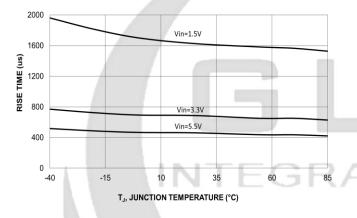


Figure 22. Vout Rise Time vs. Temperature

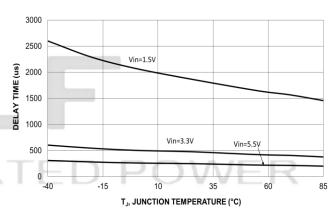


Figure 13. Turn-On Delay Time vs. Temperature

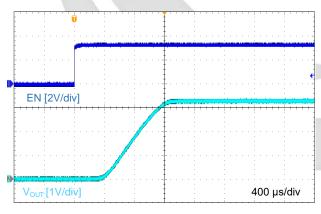


Figure 16. Turn-On Response, GLF1110 VIN=3.3 V, CIN=0.1 uF, COUT=0.1 uF, RL=150 Ω

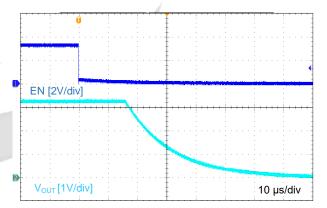


Figure 17. Turn-Off Response, GLF1110 VIN=3.3 V, CIN=0.1 uF, COUT=0.1 uF, RL=150  $\Omega$ 

## GLF1110, GLF1111

## Nano-Current Power IoSmart<sup>™</sup> Load Switch

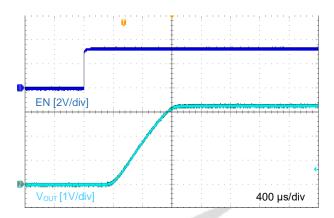


Figure 14. Turn-On Response, GLF1111 VIN=3.3 V, CIN=0.1 uF, COUT=0.1 uF, RL=150  $\Omega$ 

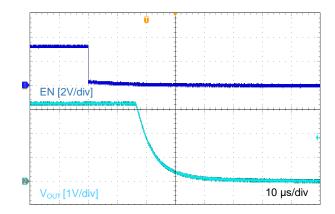


Figure 15. Turn-Off Response, GLF1111 VIN=3.3 V, CIN=0.1 uF, COUT=0.1 uF, RL=150  $\Omega$ 

## APPLICATION INFORMATION

The GLF1110 / GLF1111 is an integrated 2 A, Ultra-Efficient I<sub>Q</sub>Smart<sup>™</sup> Load Switch devices with a fixed slew rate control to limit the inrush current during turn on. Each device is capable of operating over a wide input range from 1.5 V to 5.5 V with very low on-resistance to reduce conduction loss. In the off state, these devices consume very low leakage current to avoid unwanted standby current and save limited input power.

## **Input Capacitor**

The GLF1110 / GLF1111 does not require an input capacitor. However, to reduce the voltage drop on the input power rail caused by transient inrush current at start-up, a 0.1 uF capacitor is recommended to be placed close to the V<sub>IN</sub> pin. A higher input capacitor value can be used to further attenuate the input voltage drop.

## **Output Capacitor**

The GLF1110 / GLF1111 does not require an output capacitor. However, use of an output capacitor is recommended to mitigate voltage undershoot on the output pin when the switch is turning off. Undershoot can be caused by parasitic inductance from board traces or intentional load inductances. If load inductances do exist, use of an output capacitor can improve output voltage stability and system reliability. The Cout capacitor should be spaced close to the VOUT and GND pins.

### EN pin

The GLF1110 / GLF1111 can be activated by forcing EN pin high level. Note that the EN pin has an internal pull-down resistor to help pull the main switch to a known "off state" when no EN signal is applied from an external controller.

## **Output Discharge Function**

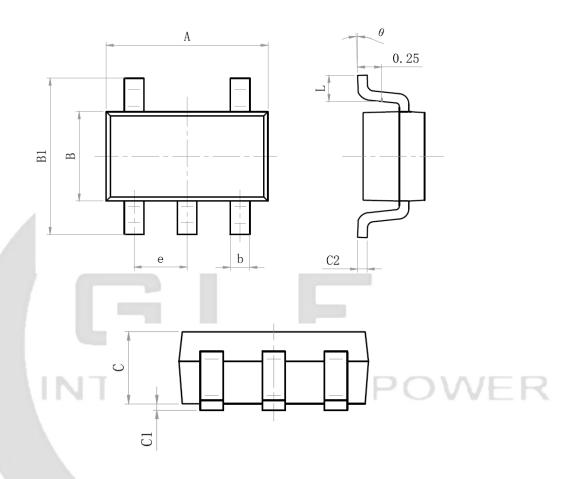
The GLF1111 has an internal discharge N-channel FET switch on the VOUT pin. When EN signal turns the main power FET to an off state, the N-channel switch turns on to discharge an output capacitor quickly.

## **Board Layout**

All traces should be as short as possible to minimize parasitic inductance effects. Wide traces for VIN, VOUT, and GND will help reduce signal degradation and parasitic effects during dynamic operation as well as improve the thermal performance at high load current.



## **PACKAGE OUTLINE**



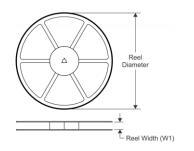
Size	Min(mm)	Min(mm) Max(mm) Mar		Min(mm)	Max(mm)
A	2.82	3.02	С	1.05	1. 15
е	0.9	95 (BSC)	C1	0.03	0. 15
b	0. 28	0.45	C2	0.12	0.23
В	1.50	1.70	L	0.35	0.55
B1	2.60	3.00	θ	0°	8°

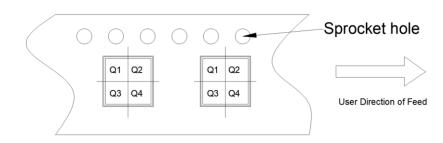


## TAPE AND REEL INFORMATION

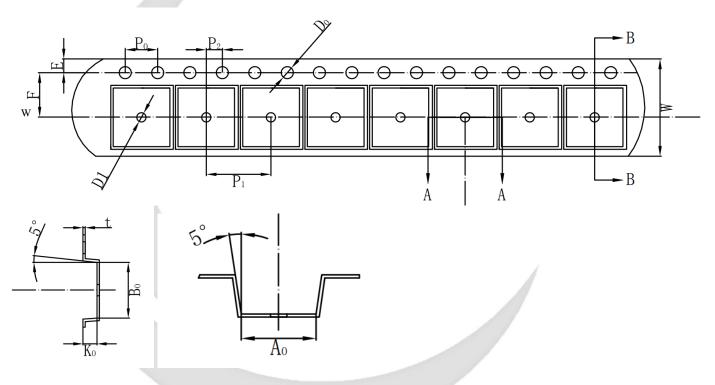
## **REEL DIMENSIONS**

## **QUADRANT ASSIGNMENTS PIN 1 ORIENTATION TAPE**





#### **TAPE DIMENSIONS**



Device	Package	Pins	SPQ	Reel Diameter(mm)	Reel Width W1	Α0	В0	K0	P1	w	Pin1
GLF1110-T1G7	SOT23-5	5	3000	178	9	3.25	3.30	1.38	4	8	Q3
GLF1111-T1G7	SOT23-5	5	3000	178	9	3.25	3.30	1.38	4	8	Q3

### Remark:

- A0: Dimension designed to accommodate the component width
- B0: Dimension designed to accommodate the component length
- C0: Dimension designed to accommodate the component thickness
- W: Overall width of the carrier tape
- P1: Pitch between successive cavity centers

## GLF1110, GLF1111

## SPECIFICATION DEFINITIONS

Document Type	Meaning	Product Status
Target Specification	This is a target specification intended to support exploration and discussion of critical needs for a proposed or target device. Spec limits including typical, minimum, and maximum values are desired, or target, limits. GLF reserves the right to change limits at any time without warning or notification. A target specification in no way guarantees future production of the device in question.	Design / Development
Preliminary Specification	This is a draft version of a product specification. The specification is still under internal review and subject to change. GLF reserves the right to change the specification at any time without warning or notification. A preliminary specification in no way guarantees future production of the device in question.	Qualification
Product Specification	This document represents the anticipated production performance characteristics of the device.	Production

## **DISCLAIMERS**

Information in this document is believed to be accurate and reliable, however GLF assumes no liability for errors or omissions. Device performance may be impacted by testing methods and application use cases. Users are responsible to independently evaluate the applicability, usability, and suitability of GLF devices in their application. In no case will GLF be liable for incidental, indirect, or consequential damages associated with the use, mis-use, or sale of its product. Customers are wholly responsible to assure GLF devices meet their system level and end product requirements. GLF retains the right to change the information provided in this data sheet without notice.